











TPA6133A2

ZHCSBA5B - JUNE 2013 - REVISED SEPTEMBER 2014

TPA6133A2 138mW DirectPath™ 立体声耳机放大器

特性

- DirectPath™ 接地基准输出
 - 免除了对输出直流 (DC) 阻断电容器的需要
 - 减少了电路板面积
 - 减少了组件高度和成本
 - 无衰减的全低音响应
- 电源电压范围: 2.5V 至 5.5V
- 高电源抑制比 (> 100dB PSRR)
- 针对最大噪声抑制的差分输入(69dB 共模抑制比 (CMRR))
- 禁用后保持高阻抗输出
- 高级爆音/喀嗒噪声抑制电路
- 针对关断的通用输入输出 (GPIO) 控制
- 20 引脚, 4mm x 4mm 超薄四方扁平无引线 (WQFN) 封装

2 应用范围

- 移动电话
- 音频耳机
- 笔记本电脑
- 高保真应用

简化应用示意图

3 说明

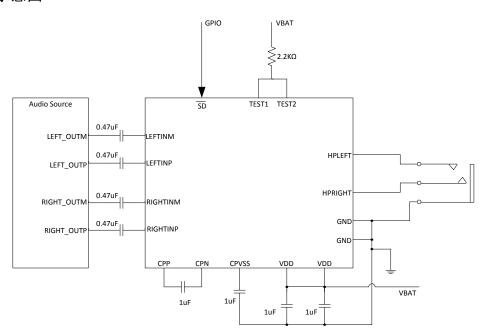
TPA6133A2是一款具有 GPIO 控制的立体声 DirectPath™ 头戴式耳机放大器。 TPA6133A2具有最 小的静态流耗, Inn的典型值为 4.2mA, 这使得它非常 适合于便携式应用。 GPIO 控制使得此器件能够被置 于低功耗关断模式中。

TPA6133A2是一款信噪比为 93dB 的高保真放大器。 大于 100dB 的 PSRR 可在不影响收听体验的同时实现 与电池的直接连接。 12 μVrms 的输出噪声(典型值输 入信噪比 (A-weighted)) 在默声周期期间提供最小的噪 声背景。 可配置差分输入和高 CMRR 可在一个移动器 件所处的嘈杂环境中实现最大噪声抑制。

器件信息(1)

部件号	封装	封装尺寸 (标称值)
TPA6133A2	超薄四方扁平无引线 (WQFN) (20)	4.00mm x 4.00mm

(1) 如需了解所有可用封装,请见数据表末尾的可订购产品附录。





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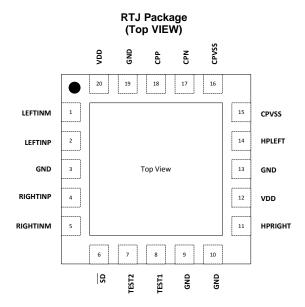
5 修订历史记录

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

CI	hanges from Revision A (August 2014) to Revision B	Page
•	Changed "PIN QFN" To: "NUMBER" in the Pin Functions table	3
•	Added a NOTE to the Applications and Implementation section	13
•	Added new paragraph to the Application Information section	13
CI	hanges from Original (June 2013) to Revision A	Page
•	添加了处理额定值表,特性描述部分,器件功能模式,应用和实施部分,电源相关建议部分,布局部分,器件和文档 支持部分以及机械、封装和可订购信息部分。	1
•	添加了器件信息表	1
•	Moved "Minimum Load Impedance" From the Absolute Maximum Ratings table To the Recommended Operating Conditions table	4
•	Added the Thermal Information Table	4
•	Changed text in the Overview section From: "toggling the \overline{SD} pin to logic 1." To: "asserting the \overline{SD} pin to logic 1."	10
•	Changed text in the Headphone Amplifier section From: "the output signal is severely clipped" To: "power consumption will be higher"	11
•	Added the Optional Test Setup section	15
•	Added the Layout Example image	17



6 Pin Configuration and Functions



Pin Functions

PIN	1	INPUT,			
NAME	NUMBER	OUTPUT, POWER	DESCRIPTION		
LEFTINM	1	I	Left channel negative differential input. Impedance must be matched to LEFTINP. Connect the left input to LEFTINM when using single-ended inputs.		
LEFTINP	2	I	Left channel positive differential input. Impedance must be matched to LEFTINM. AC ground LEFTINP near signal source while maintaining matched impedance to LEFTINM when using single ended inputs.		
RIGHTINP	4	I	Right channel positive differential input. Impedance must be matched to RIGHTINM. AC ground RIGHTINP near signal source while maintaining matched impedance to RIGHTINM when using single-ended inputs.		
GND	3, 9, 10, 13	Р	Analog ground. Must be connected to common supply GND. It is recommended that this pin be used to decouple V_{DD} for analog. Use pin 13 to decouple pin 12 on the QFN package.		
RIGHTINM	5	ı	Right channel negative differential input. Impedance must be matched to RIGHTINP. Connect the right input to RIGHTINM when using single-ended inputs.		
SD	6	1	Shutdown. Active low logic. 5V tolerant input.		
TEST2	7	1	Factory test pins. Pull up to VDD supply. See Applications Diagram.		
TEST1	8	1	Factory test pins. Pull up to VDD supply. See Applications Diagram.		
HPRIGHT	11	0	Headphone light channel output. Connect to the right terminal of the headphone jack.		
V _{DD}	12	Р	Analog V_{DD} . V_{DD} must be connected to common V_{DD} supply. Decouple with its own 1- μ F capacitor to analog ground (pin 13).		
HPLEFT	14	0	Headphone left channel output. Connect to left terminal of headphone jack.		
CPVSS	15, 16	Р	Negative supply generated by the charge pump. Decouple to pin 19 or a GND plane. Use a 1 μ F capacitor.		
CPN	17	Р	Charge pump flying capacitor negative terminal. Connect one side of the flying capacitor to CPN.		
CPP	18	Р	Charge pump flying capacitor positive terminal. Connect one side of the flying capacitor to CPP.		
GND	19	Р	Charge pump ground. GND must be connected to common supply GND. It is recommended that this pin be decoupled to the V_{DD} of the charge pump pin (pin 20 on the QFN).		
V _{DD}	20	Р	Charge pump voltage supply. V_{DD} must be connected to the common V_{DD} voltage supply. Decouple to GND (pin 19) with its own 1 μ F capacitor.		
Thermal pad	Die Pad	Р	Solder the thermal pad on the bottom of the QFN package to the GND plane of the PCB. It is required for mechanical stability and will enhance thermal performance.		



7 Specification

7.1 Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range, T_A = 25°C (unless otherwise noted)

		MIN	MAX	UNIT
Supply voltage, V _{DD}		-0.3	6	V
Input voltage RIGHTINx, LEFTINx			CPVSS-0.2 V to minimum of (3.6 V, VDD+0.2 V)	
	SD, TEST1, TEST2	-0.3	7	V
Output continuous total power dissipation		See the Therma	Information Table	
Operating free-air temperature range, T _A		-40	85	°C
Operating junction temperature range, T_{J}		-40	150	°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 Handling Ratings

			MIN	MAX	UNIT
T _{stg}	Storage temperature rang	e e	-65	150	°C
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	-3	3	kV
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins (2)	-750	750	V

JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

			MIN	MAX	UNIT
	Supply voltage, V _{DD}		2.5	5.5	V
V _{IH}	High-level input voltage	TEST1, TEST2, SD	1.3		V
V_{IL}	Low-level input voltage	SD		0.35	V
	Minimum Load Impedance		12.8		Ω
T _A	Operating free-air temperatur)	-40	85	°C

7.4 Thermal Information

	TUEDMAL METRIC(1)		
	THERMAL METRIC ⁽¹⁾	20 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	34.8	
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	32.5	
$R_{\theta JB}$	Junction-to-board thermal resistance	11.6	°C/W
ΨЈТ	Junction-to-top characterization parameter	0.4	*C/VV
ΨЈВ	Junction-to-board characterization parameter	11.6	
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	3.1	

⁽¹⁾ For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.



7.5 Electrical Characteristics

 $T_A = 25^{\circ}C$ (unless otherwise noted)

· A =0	A 10 C (dimess cities insists)						
	PARAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Vos	Output offset voltage	V _{DD} = 2.5 V to 5.5 V, inputs grounded			135	400	μV
PSRR	DC Power supply rejection ratio	V _{DD} = 2.5 V to 5.5 V, inputs grounded			-101	-85	dB
CMRR	Common mode rejection ratio	V _{DD} = 2.5 V to 5.5 V			-69		dB
	I Pak Janet Sanat assess	V 55V V V	TEST1, TEST2			1	^
I _{IH}	High-level input current	$V_{DD} = 5.5 \text{ V}, V_{I} = V_{DD}$	SD			10	μA
I _{IL}	Low-level input current	V _{DD} = 5.5 V, V _I = 0 V	SD			1	μΑ
	Cumply ourrent	$V_{DD} = 2.5 \text{ V to } 5.5 \text{ V}, \overline{SD} = V_{DD}$	•		4.2	6	mA
IDD	Supply current	Shutdown mode, $V_{DD} = 2.5V$ to 5.5 V,	SD = 0 V		0.08	1	μΑ

7.6 Operating Characteristics

 V_{DD} = 3.6 V , T_A = 25°C, R_L = 16 Ω (unless otherwise noted)

	PARAMETER	TEST CONDITION	ONS	MIN TY	MAX	UNIT
Po	Output power	Stereo, Outputs out of phase,	$V_{DD} = 2.5V$ $V_{DD} = 3.6V$	6		mW
. 0		THD = 1%, f = 1 kHz, Gain = +4 dB	$V_{DD} = 5V$	14		
			f = 100 Hz	0.00969	6	
THD+N	HD+N Total harmonic distortion plus noise	P _O = 35 mW	f = 1 kHz	0.0079	o o	
	plus fioloc		f = 20 kHz	0.00219	o o	
		200 mV _{pp} ripple, f = 217 Hz	00 mV _{pp} ripple, f = 217 Hz		3 -85	
k_{SVR}	Supply ripple rejection ratio	200 mV _{pp} ripple, f = 1 kHz		-9	2	dB
		200 mV _{pp} ripple, f = 20 kHz	• •		1	
A_{v}	Channel DC Gain	$\overline{SD} = V_{DD}$		1.59	7	V/V
ΔA_{v}	Gain matching			0.19	, 0	
	Slew rate			0.	4	V/µs
V _n	Noise output voltage	V _{DD} = 3.6V, A-weighted, Gain = +4 dB	3	1	2	μV_{RMS}
f _{osc}	Charge pump switching frequency			300 38	1 500	kHz
	Start-up time from shutdown			4.	3	ms
	Differential input impedance			36.	6	kΩ
SNR	Signal-to-noise ratio	P _o = 35 mW		9	3	dB
	The war all about decome	Threshold		18)	°C
	Thermal shutdown	Hysteresis		3	5	°C
Z _O	HW Shutdown HP output impedance	$\overline{SD} = 0 \text{ V}$, measured output to ground		11	2	Ω
Co	Output capacitance			8)	pF



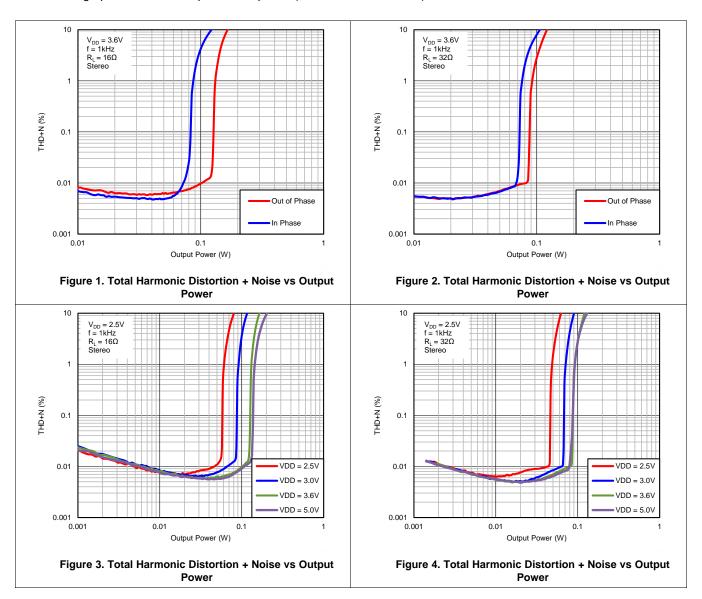
7.7 Typical Characteristics

Table 1. Table of Graphs

		Figure
Total harmonic distortion + noise	versus Output power	Figure 1–Figure 4
Total harmonic distortion + noise	versus Frequency	Figure 5–Figure 12
Supply voltage rejection ratio	versus Frequency	Figure 13-Figure 14
Common mode rejection ratio	versus Frequency	Figure 15-Figure 16
Crosstalk	versus Frequency	Figure 17-Figure 18

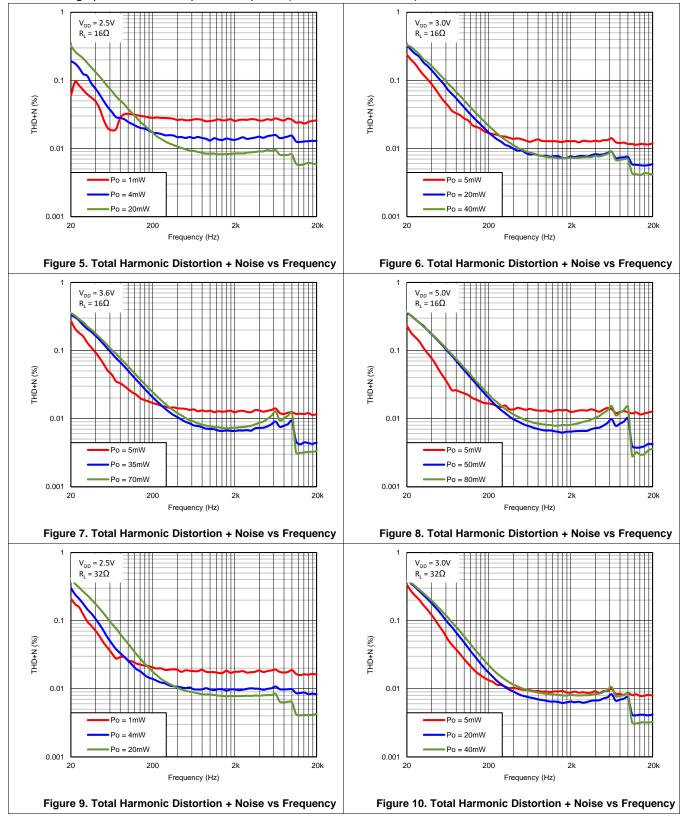
 $C_{(PUMP,\ DECOUPLE,\ ,BYPASS,\ CPVSS)} = 1\ \mu F,\ C_I = 2.2\ \mu F.$

All THD + N graphs taken with outputs out of phase (unless otherwise noted).



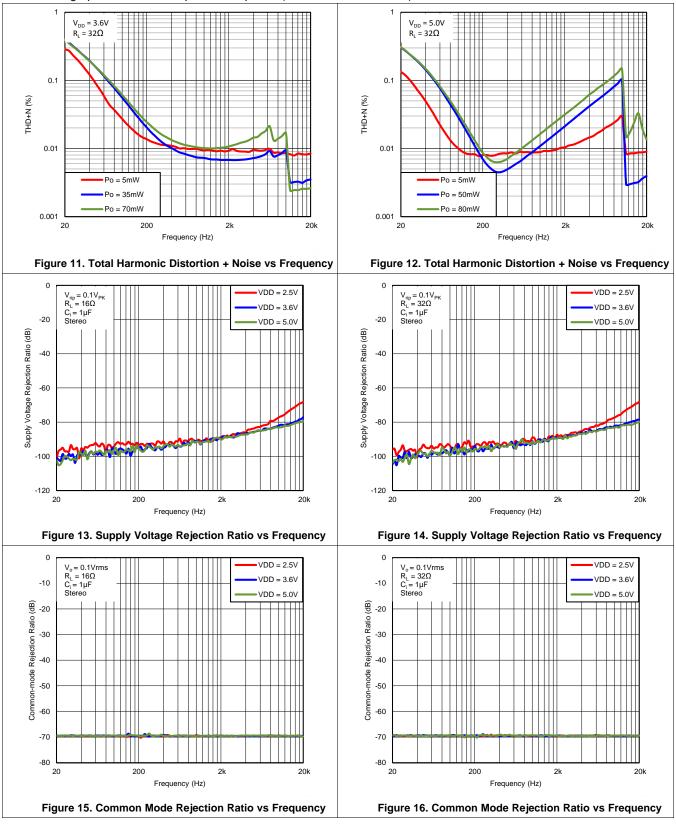


All THD + N graphs taken with outputs out of phase (unless otherwise noted).



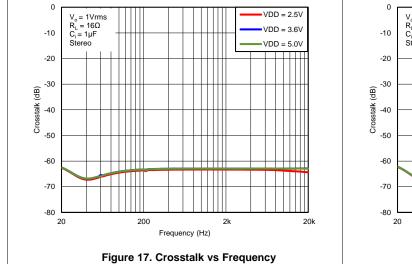


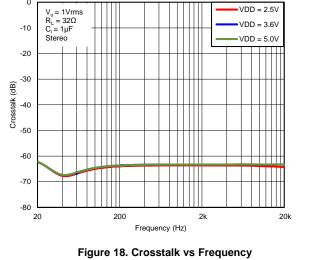
All THD + N graphs taken with outputs out of phase (unless otherwise noted).





All THD + N graphs taken with outputs out of phase (unless otherwise noted).





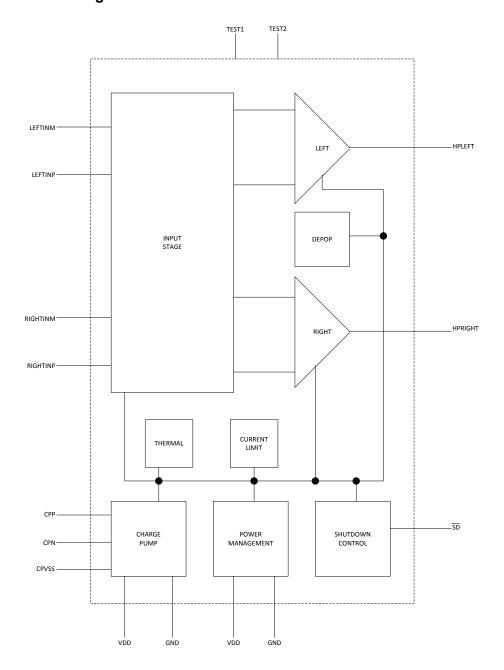


8 Detailed Description

8.1 Overview

Headphone channels and the charge pump are activated by asserting the \overline{SD} pin to logic 1. The charge pump generates a negative supply voltage for the output amplifiers. This allows a 0 V bias at the outputs, eliminating the need for bulky output capacitors. The thermal block detects faults and shuts down the device before damage occurs. The current limit block prevents the output current from getting high enough to damage the device. The De-Pop block eliminates audible pops during power-up, power-down, and amplifier enable and disable events.

8.2 Functional Block Diagram





8.3 Feature Description

8.3.1 Headphone Amplifiers

Single-supply headphone amplifiers typically require dc-blocking capacitors. The capacitors are required because most headphone amplifiers have a dc bias on the outputs pin. If the dc bias is not removed, power consumption will be higher, and large amounts of dc current rush through the headphones, potentially damaging them. The top drawing in Figure 19 illustrates the conventional headphone amplifier connection to the headphone jack and output signal.

DC blocking capacitors are often large in value. The headphone speakers (typical resistive values of 16 Ω or 32 Ω) combine with the dc blocking capacitors to form a high-pass filter. Equation 1 shows the relationship between the load impedance (R_L), the capacitor (C_O), and the cutoff frequency (f_C).

$$f_{c} = \frac{1}{2\pi R_{L} C_{O}} \tag{1}$$

Co can be determined using Equation 2, where the load impedance and the cutoff frequency are known.

$$C_{O} = \frac{1}{2\pi R_{L} f_{c}} \tag{2}$$

If f_c is low, the capacitor must then have a large value because the load resistance is small. Large capacitance values require large package sizes. Large package sizes consume PCB area, stand high above the PCB, increase cost of assembly, and can reduce the fidelity of the audio output signal.

Two different headphone amplifier applications are available that allow for the removal of the output dc blocking capacitors. The capless amplifier architecture is implemented in the same manner as the conventional amplifier with the exception of the headphone jack shield pin. This amplifier provides a reference voltage, which is connected to the headphone jack shield pin. This is the voltage on which the audio output signals are centered. This voltage reference is half of the amplifier power supply to allow symmetrical swing of the output voltages. Do not connect the shield to any GND reference or large currents will result. The scenario can happen if, for example, an accessory other than a floating GND headphone is plugged into the headphone connector. See the second block diagram and waveform in Figure 19.



Feature Description (continued)

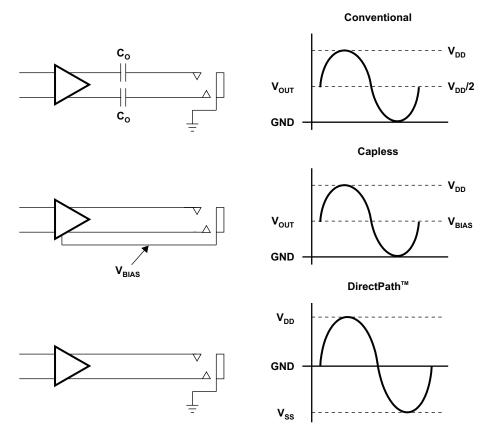


Figure 19. Amplifier Applications

The DirectPath™ amplifier architecture operates from a single supply but makes use of an internal charge pump to provide a negative voltage rail. Combining the user provided positive rail and the negative rail generated by the IC, the device operates in what is effectively a split supply mode. The output voltages are now centered at zero volts with the capability to swing to the positive rail or negative rail. The DirectPath™ amplifier requires no output dc blocking capacitors, and does not place any voltage on the sleeve. The bottom block diagram and waveform of Figure 19 illustrate the ground-referenced headphone architecture. This is the architecture of the TPA6133A2.

8.4 Device Functional Modes

8.4.1 Modes of Operation

The TPA6133A2 supports two modes of operation. When the \overline{SD} pin is driven to logic 0, the device is in low power mode where the charge pump is powered down, the headphone channel is disabled and the outputs are pulled to ground. When the \overline{SD} pin is driven to logic 1, the device enters an active mode with charge pump powered up and headphone channel enabled with channel gain of +4dB. The transition from inactive to active and active to inactive states is done softly to avoid audible artifacts.



9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The TPA6133A2 is a stereo DirectPath[™] headphone amplifier with GPIO control. The TPA6133A2 has minimal quiescent current consumption, with a typical I_{DD} of 4.2 mA, making it optimal for portable applications.

9.2 Typical Application

Figure 20 shows a typical application circuit for the TPA6133A2 with a stereo headphone jack and supporting power supply decupling capacitors.

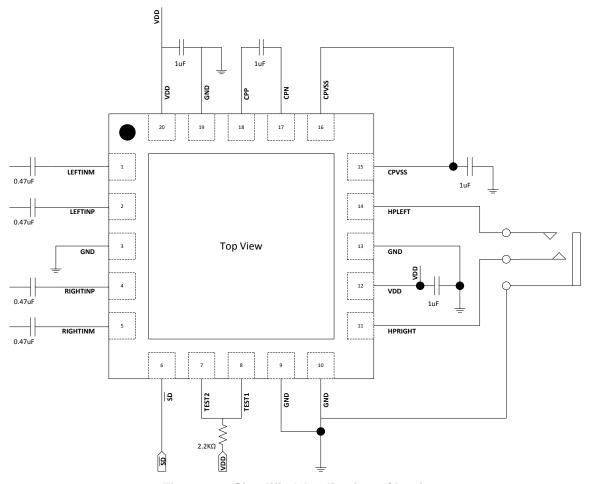


Figure 20. Simplified Applications Circuit



Typical Application (continued)

9.2.1 Design Requirements

For this design example, use the following as the input parameters.

Table 2. Design Parameters

DESIGN PARAMTER	EXAMPLE VALUE
Input voltage	2.5 V – 5.5 V
Minimum current limit	4 mA
Maximum current limit	6 mA

9.2.2 Detailed Design Procedure

9.2.2.1 Input-Blocking Capacitors

DC input-blocking capacitors block the dc portion of the audio source, and allow the inputs to properly bias. Maximum performance is achieved when the inputs of the TPA6133A2 are properly biased. Performance issues such as pop are optimized with proper input capacitors.

The dc input-blocking capacitors may be removed provided the inputs are connected differentially and within the input common mode range of the amplifier, the audio signal does not exceed ±3 V, and pop performance is sufficient.

 C_{IN} is a theoretical capacitor used for mathematical calculations only. Its value is the series combination of the dc input-blocking capacitors, $C_{(DCINPUT-BLOCKING)}$. Use Equation 3 to determine the value of $C_{(DCINPUT-BLOCKING)}$. For example, if C_{IN} is equal to 0.22 μ F, then $C_{(DCINPUT-BLOCKING)}$ is equal to about 0.47 μ F.

$$C_{IN} = \frac{1}{2} C_{(DCINPUT-BLOCKING)}$$
(3)

The two $C_{(DCINPUT\text{-}BLOCKING)}$ capacitors form a high-pass filter with the input impedance of the TPA6133A2. Use Equation 3 to calculate C_{IN} , then calculate the cutoff frequency using C_{IN} and the differential input impedance of the TPA6133A2, R_{IN} , using Equation 4. Note that the differential input impedance changes with gain. The frequency and/or capacitance can be determined when one of the two values are given.

$$fc_{IN} = \frac{1}{2\pi R_{IN} C_{IN}}$$
 or $C_{IN} = \frac{1}{2\pi fc_{IN} R_{IN}}$ (4)

If a high pass filter with a -3 dB point of no more than 20 Hz is desired over all gain settings, the minimum impedance would be used in the above equation. The capacitor value by the above equation would be 0.215 μ F. However, this is C_{IN}, and the desired value is for C_(DCINPUT-BLOCKING). Multiplying C_{IN} by 2 yields 0.43 μ F, which is close to the standard capacitor value of 0.47 μ F. Place 0.47 μ F capacitors at each input terminal of the TPA6133A2 to complete the filter.

9.2.2.2 Charge Pump Flying Capacitor and CPVSS Capacitor

The charge pump flying capacitor serves to transfer charge during the generation of the negative supply voltage. The CP_{VSS} capacitor must be at least equal to the flying capacitor in order to allow maximum charge transfer. Low ESR capacitors are an ideal selection, and a value of 1 μ F is typical.

9.2.2.3 Decoupling Capacitors

The TPA6133A2 is a DirectPathTM headphone amplifier that requires adequate power supply decoupling to ensure that the noise and total harmonic distortion (THD) are low. Use good low equivalent-series-resistance (ESR) ceramic capacitors, typically 1.0 μ F. Find the smallest package possible, and place as close as possible to the device V_{DD} lead. Placing the decoupling capacitors close to the TPA6133A2 is important for the performance of the amplifier. Use a 10 μ F or greater capacitor near the TPA6133A2 to filter lower frequency noise signals. The high PSRR of the TPA6133A2 will make the 10 μ F capacitor unnecessary in most applications.



9.2.2.4 Optional Test Setup

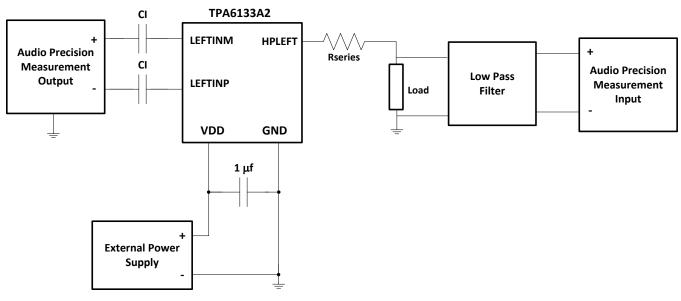


Figure 21. Test Setup

NOTE

Separate power supply decoupling caps are used on all VDD and CPVSS Pins The low pass filter is used to remove harmonic content above the audible range.



9.2.3 Application Curves

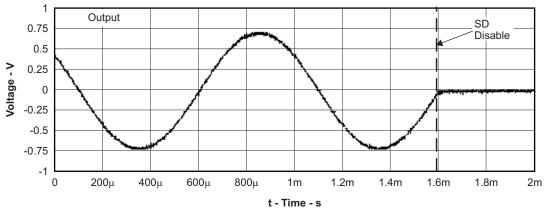


Figure 22. Shutdown Time

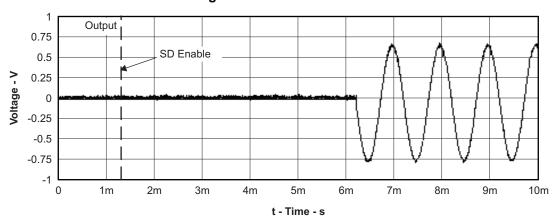


Figure 23. Startup Time

10 Power Supply Recommendations

The device is designed to operate from an input voltage supply range of 2.5 V to 5.5 V. Therefore, the output voltage range of power supply should be within this range and well regulated. The current capability of upper power should not exceed the max current limit of the power switch.



11 Layout

11.1 Layout Guidelimes

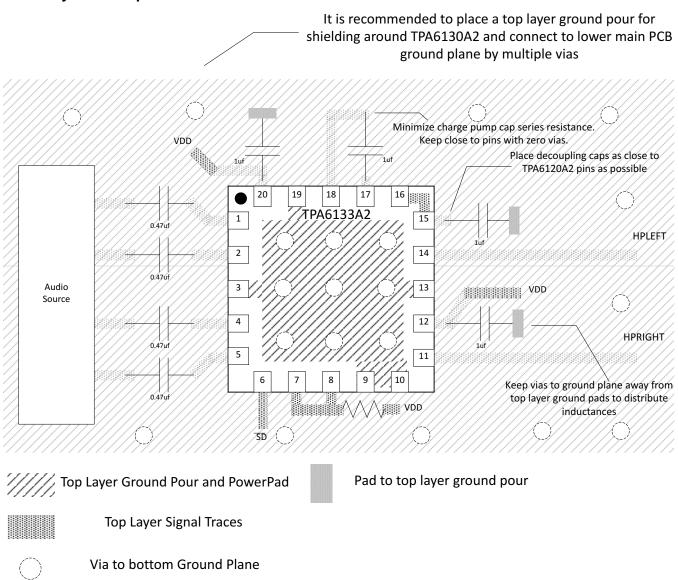
11.1.1 Exposed Pad On TPA6133A2RTJ Package

- Solder the exposed metal pad on the TPA6133A2RTJ QFN package to the a pad on the PCB. The pad on the PCB may be grounded or may be allowed to float (not be connected to ground or power).
- If the pad is grounded, it must be connected to the same ground as the GND pins (3, 9, 10, 13, and 19). See the layout and mechanical drawings at the end of the datasheet for proper sizing.
- Soldering the thermal pad improves mechanical reliability, improves grounding of the device, and enhances thermal conductivity of the package.

11.1.2 GND Connections

 The GND pin for charge pump should be decoupled to the charge pump V_{DD} pin, and the GND pin adjacent to the Analog V_{DD} pin should be separately decoupled to each other.

11.2 Layout Example





12 器件和文档支持

12.1 商标

DirectPath is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

12.2 静电放电警告



这些装置包含有限的内置 ESD 保护。 存储或装卸时,应将导线一起截短或将装置放置于导电泡棉中,以防止 MOS 门极遭受静电损伤。

12.3 术语表

SLYZ022 — TI 术语表。

这份术语表列出并解释术语、首字母缩略词和定义。

13 机械封装和可订购信息

以下页中包括机械封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本,请查阅左侧的导航栏。

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数据转换器	www.ti.com.cn/dataconverters	消费电子	www.ti.com/consumer-apps
DLP® 产品	www.dlp.com	能源	www.ti.com/energy
DSP - 数字信号处理器	www.ti.com.cn/dsp	工业应用	www.ti.com.cn/industrial
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PACKAGE OPTION ADDENDUM

5-Feb-2021

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
HPA022642RTJR	ACTIVE	QFN	RTJ	20	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	SIZ	Samples
TPA6133A2RTJR	ACTIVE	QFN	RTJ	20	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	SIZ	Samples
TPA6133A2RTJT	ACTIVE	QFN	RTJ	20	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	SIZ	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

5-Feb-2021

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

www.ti.com 16-Feb-2019

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter	Reel Width	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
					(mm)	W1 (mm)						
TPA6133A2RTJR	QFN	RTJ	20	3000	330.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2
TPA6133A2RTJT	QFN	RTJ	20	250	180.0	12.4	4.25	4.25	1.15	8.0	12.0	Q2

www.ti.com 16-Feb-2019



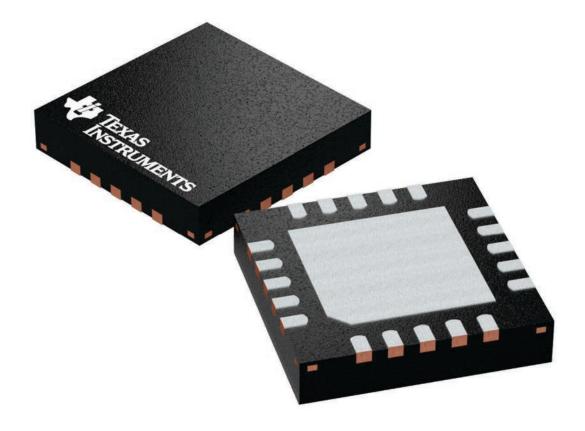
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPA6133A2RTJR	QFN	RTJ	20	3000	367.0	367.0	35.0
TPA6133A2RTJT	QFN	RTJ	20	250	210.0	185.0	35.0

4 x 4, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

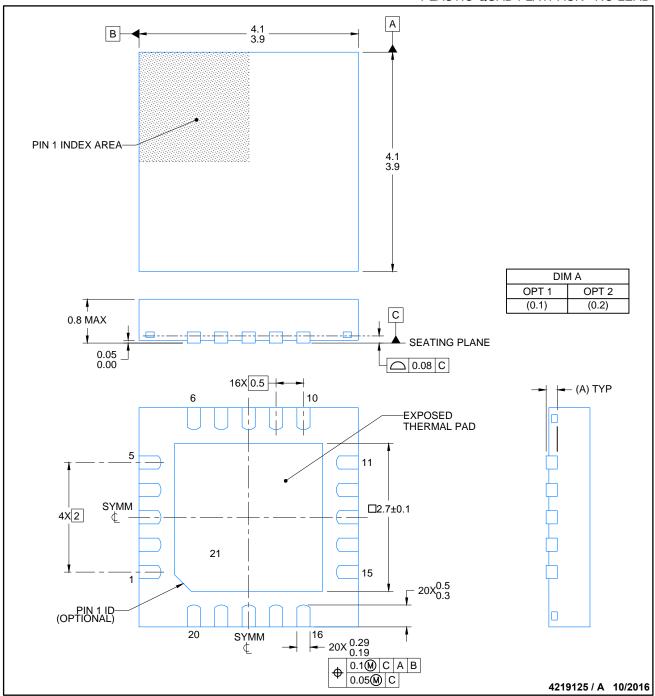


DATA BOOK PACKAGE OUTLINE

LEADFRAME EXAMPLE 4222370

DRAFTSMAN: H. DENG	DATE: 09/12/2016	DIMENSIONS IN MILLIMETERS
DESIGNER: H. DENG	DATE: 09/12/2016	
CHECKER: V. PAKU & T. LEQUANG	DATE: 09/12/2016	SEMICONDUCTOR OPERATIONS 01295
ENGINEER: T. TANG	DATE: 09/12/2016	ePOD, RTJ0020D / WQFN,
APPROVED: E. REY & D. CHIN	DATE: 10/06/2016	20 PIN, 0.5 MM PITCH
RELEASED: WDM	DATE: 10/24/2016	
TEMPLATE INFO: EDGE# 4218519	DATE: 04/07/2016	SCALE SIZE TO PAGE TO TO PAGE TO TO TO TO TO TO TO T

PLASTIC QUAD FLATPACK - NO LEAD

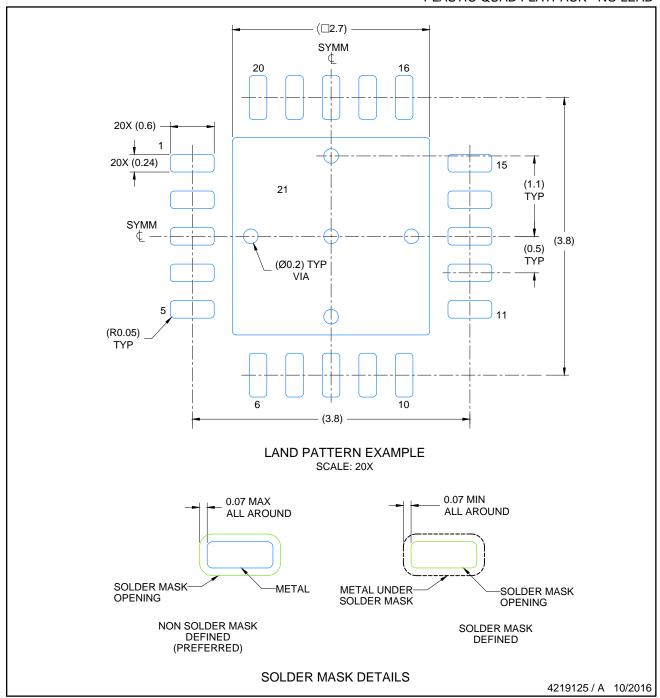


NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

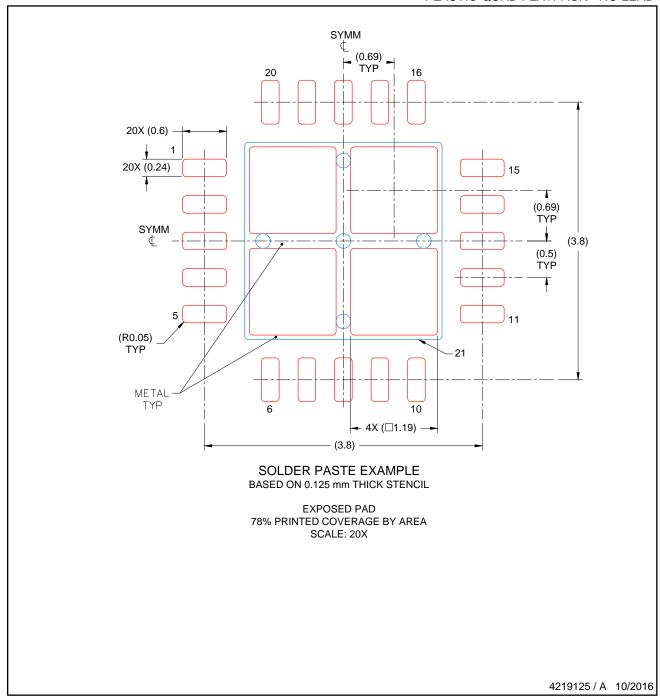


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations..



		REVISION	IS			
REV	DESCRIPTION		ECR		ENGINEER / DRAFT	
Α	RELEASE NEW DRAWING		2160736	10/24/2016	T. TANG / H. DE	
		SCALE SIZE		4040405	REV	PAGE
		NTS A		4219125	A	5 OF 5

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